11 September 2015

Product data sheet

1. General description

NPN high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

PNP complement: PHPT61003PY

2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- Power management
- Loadswitch
- Linear mode voltage regulator
- Backlighting applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	100	V
I _C	collector current		-	-	3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	8	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	90	150	mΩ
		I_C = 3 A; I_B = 300 mA; pulsed; $t_p \le$ 300 μs; $δ \le$ 0.02 ; T_{amb} = 25 °C	-	75	110	mΩ



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	C
2	E	emitter		в
3	Е	emitter	[d	, N
4	В	base		E sym123
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	Symiles

6. Ordering information

Table 3. Ordering information

Type number	Package	ackage				
	Name	Description	Version			
PHPT61003NY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT61003NY	1003NAB

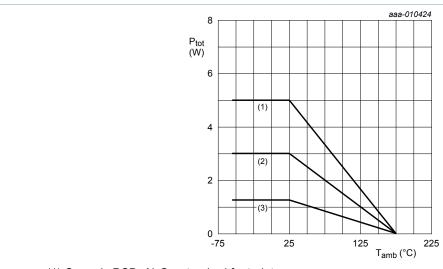
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	100	V
V _{CEO}	collector-emitter voltage	open base		-	100	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	8	Α
I _B	base current			-	0.5	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.25	W
			[2]	-	3	W
			[3]	-	5	W
			[4]	-	25	W
T _j	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB) single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic PCB; Al₂O₃; standard footprint.
- [4] Power dissipation from junction to mounting base.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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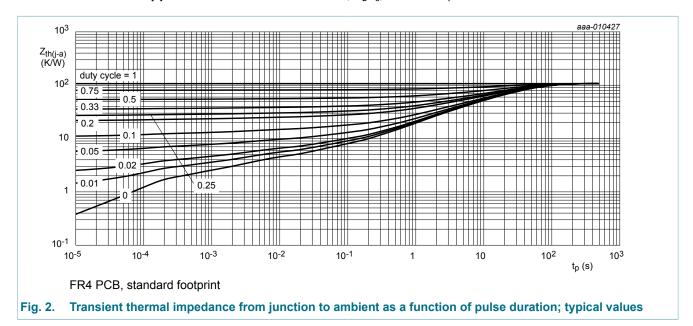
PHPT61003NY

9. Thermal characteristics

Table 6. Thermal characteristics

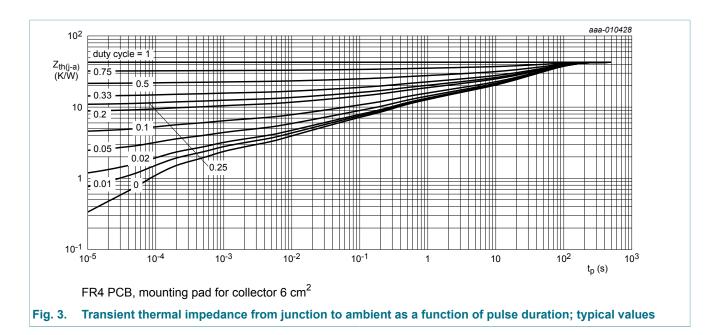
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance	in free air	[1]	-	-	115	K/W
			<u>[2]</u>	-	-	50	K/W
	ambient		[3]	-	-	30	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	6	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic PCB; Al₂O₃; standard footprint.



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100 V, 3 A NPN high power bipolar transistor



10. Characteristics

Table 7. Characteristics

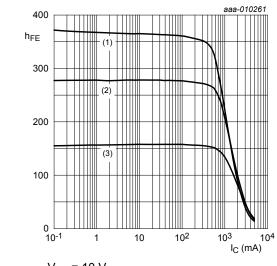
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{CBO}	collector-base cut-off	V_{CB} = 80 V; I_{E} = 0 A; T_{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 80 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 80 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 7 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 10 V; I_{C} = 500 mA; $t_{p} \le$ 300 µs; $\bar{o} \le$ 0.02 ; T_{amb} = 25 °C; pulsed	150	250	-	
		V_{CE} = 10 V; I_{C} = 1 A; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02 \ ; T_{amb}$ = 25 °C; pulsed	80	250	-	
		V_{CE} = 10 V; I_{C} = 2 A; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02 \ ; T_{amb}$ = 25 °C; pused	20	100	-	
		V_{CE} = 10 V; I_{C} = 3 A; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02 \ ; T_{amb}$ = 25 °C; pulsed	10	40	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300 \text{ μs}; \delta \le 0.02 \text{ ; } T_{amb}$ = 25 °C	-	90	150	mV
		I_C = 3 A; I_B = 300 mA; pulsed; $t_p \le 300 \text{ μs}$; $\delta \le 0.02 \text{ ; } T_{amb}$ = 25 °C	-	225	330	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02 ; T_{amb} = 25 °C	-	90	150	mΩ
		$I_C = 3 \text{ A}; I_B = 300 \text{ mA}; \text{ pulsed};$ $t_p \le 300 \mu\text{s}; \delta \le 0.02 ; T_{amb} = 25 ^{\circ}\text{C}$	-	75	110	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02 ; T_{amb} = 25 °C	-	0.86	1	V
		I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le 300 \text{ μs}$; $\delta \le 0.02 \text{ ; } T_{amb}$ = 25 °C	-	1	1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 0.1 A; T_{amb} = 25 °C	-	0.67	0.85	V
t _d	delay time	V _{CC} = 12.5 V; I _C = 1 A; I _{Bon} = 0.05 A;	-	20	-	ns
t _r	rise time	I_{Boff} = -0.05 A; T_{amb} = 25 °C	-	300	-	ns
t _{on}	turn-on time		-	320	-	ns
t _s	storage time		-	830	-	ns
t _f	fall time		-	470	-	ns
t _{off}	turn-off time		-	1300	-	ns

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C	-	140	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	11	-	pF



 V_{CE} = 10 V

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 4. DC current gain as a function of collector current; typical values

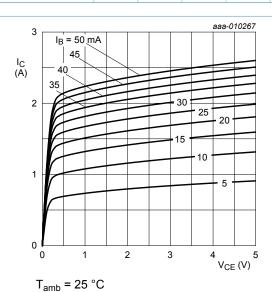
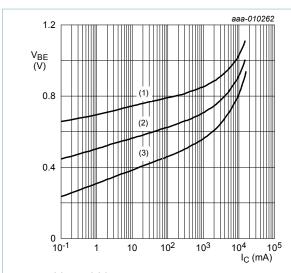


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



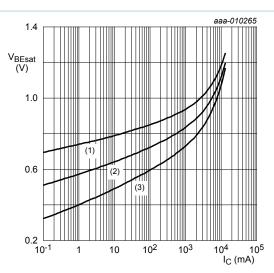
$$V_{CE} = 2 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = 100 °C

Fig. 6. Base-emitter voltage as a function of collector current; typical values



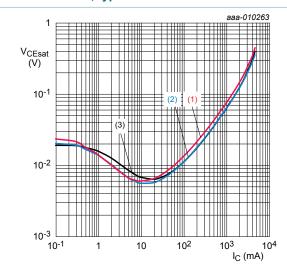
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



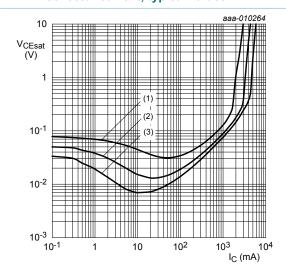
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1)
$$I_C/I_B = 50$$

(2)
$$I_C/I_B = 20$$

(3)
$$I_C/I_B = 10$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

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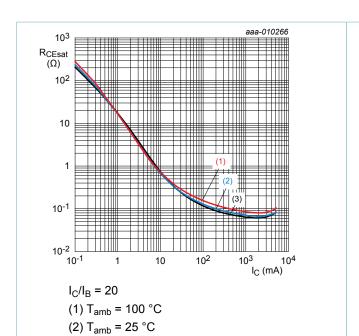


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

(3) $T_{amb} = -55 \, ^{\circ}C$

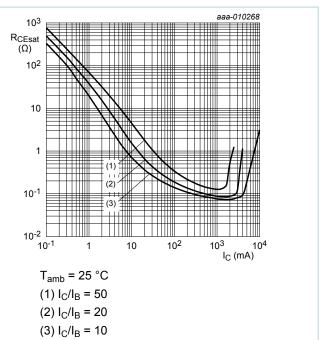
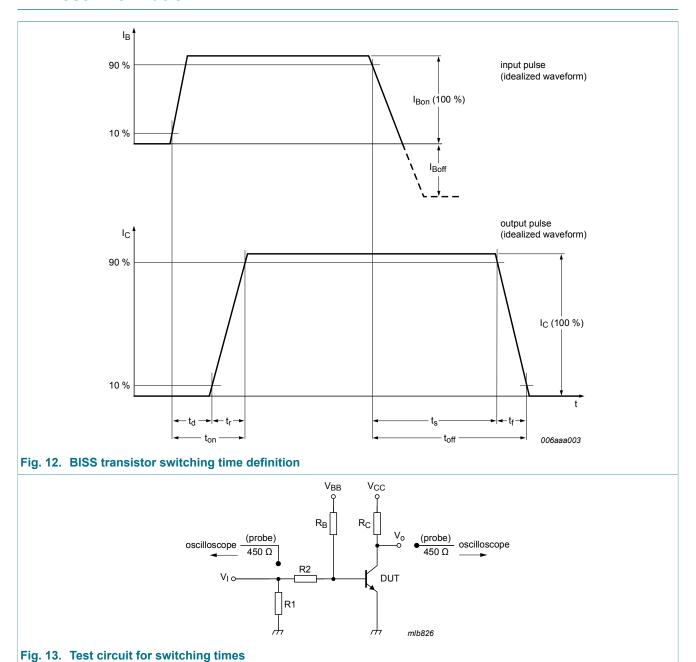


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

11. Test information



11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline

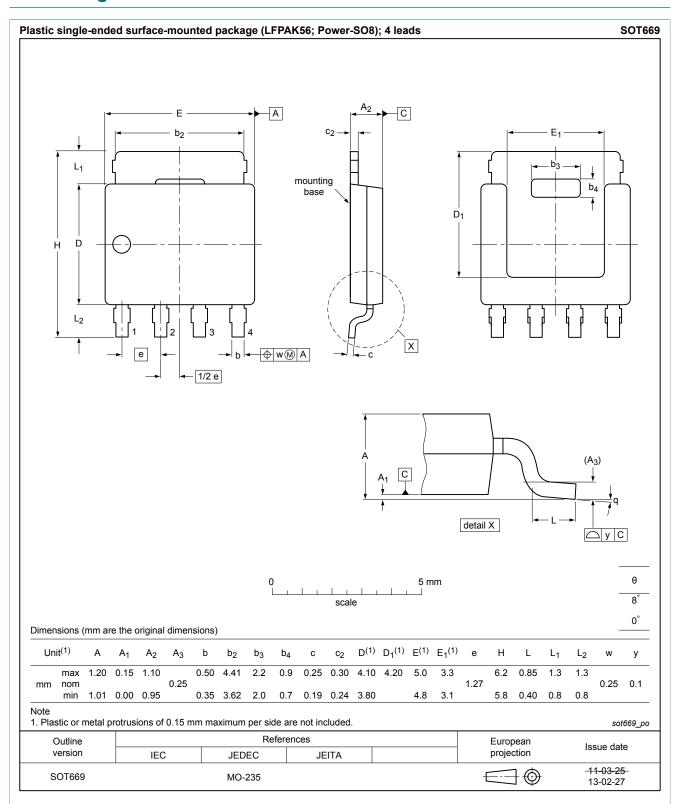


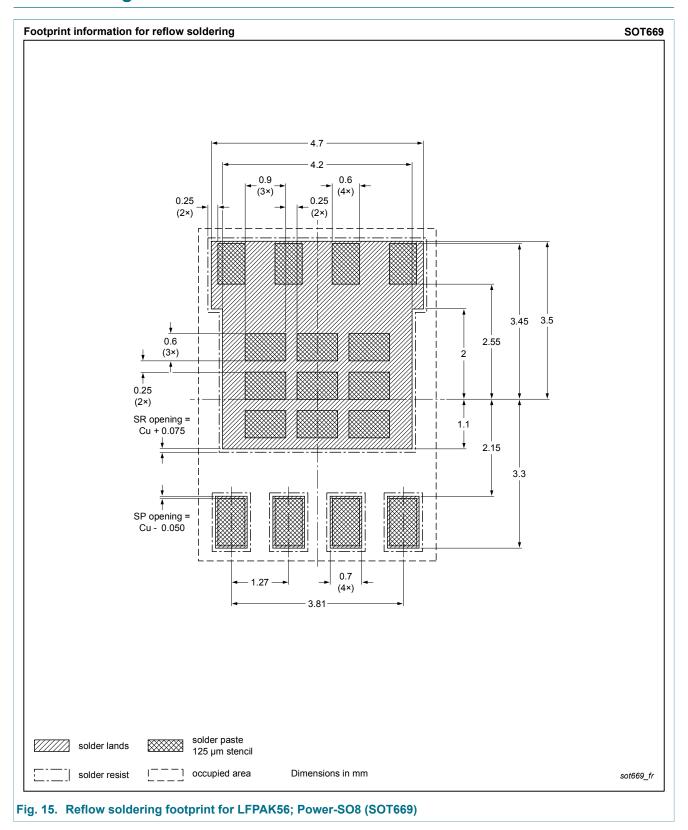
Fig. 14. Package outline LFPAK56; Power-SO8 (SOT669)

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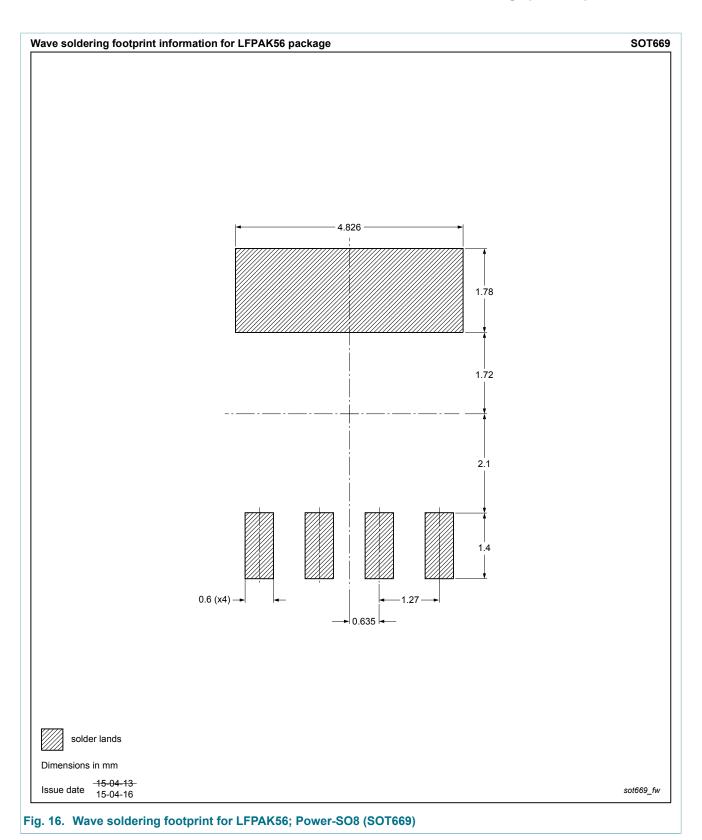
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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT61003NY v.4	20150911	Product data sheet	-	PHPT61003NY v.3
Modifications:	Editorial update ofUpdate of Figure 4	section 11. Test information	on	
PHPT61003NY v.3	20140203	Product data sheet	-	PHPT61003NY v.2
PHPT61003NY v.2	20131213	Product data sheet	-	PHPT61003NY v.1
PHPT61003NY v.1	20140113	Product data sheet	-	

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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